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means for exhausting said gas in said chamber;  
a power supply of Ultra High Frequency;  
an electromagnetic wave radiation antenna coupled to said  
power supply and installed in an atmosphere; and  
a separation plate used as dielectric between said  
antenna and the inside of said chamber, wherein  
said antenna is a microstrip antenna comprising a  
discoidal electrode.

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34. (New) A dry etching apparatus for treating a  
semiconductor wafer comprising:

a chamber;  
a holder in said chamber to receive a semiconductor  
wafer;  
means for exhausting said gas in said chamber;  
means for introducing gas into said chamber;  
a power supply of Ultra High Frequency;  
a microstrip antenna for radiating an electromagnetic  
wave, coupled to said power supply and installed in an  
atmosphere, said microstrip antenna comprising a discoidal  
electrode; and  
a separation plate used as a dielectric between said  
antenna and the inside of said chamber.

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35. (New) A dry etching apparatus according to claim 34, wherein said separation plate is a quartz disk.

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36. (New) A dry etching apparatus according to claim 34, wherein said power supply supplies power of an Ultra High Frequency band having a frequency not less than 300MHz and not more than 1GHZ.

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#### REMARKS

Claims 10-33 have been cancelled without prejudice or disclaimer as a result of being withdrawn from consideration due to a restriction requirement. Additionally, claim 5 has been cancelled without prejudice or disclaimer. Applicants have added new claims 34-36. Accordingly, claims 1, 2, 4, 6-9 and 34-36 are pending.

Claims 1-2 and 6-7 are rejected under 35 USC 102(e) as being anticipated by Yokogawa et al (US 5,891,252). Claims 4 and 8 are rejected under 35 USC 103(a) as being unpatentable over Yokogawa et al. Claim 9 is rejected under 35 USC 103(a) as being unpatentable over Yokogawa et al in view of Nakano et al (US 6,155,202). Reconsideration of these rejections is requested in view of the Continued Prosecution Application (CPA) Request filed concurrently herewith by Applicants and in view of the amendments to claim 1 and the following remarks.